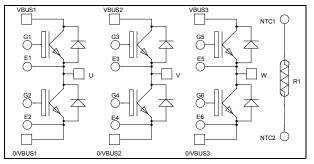
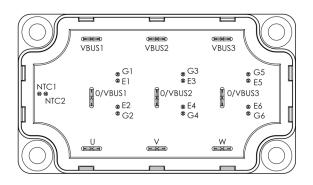


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Triple phase leg High speed Trenchstop 5 IGBT Power Module





V<sub>CES</sub> = 650V I<sub>C</sub> = 150A @ Tc = 25°C

APTGTQ150TA65TPG

#### Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

#### Features

- Trench + Field Stop IGBT5 technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 100 kHz
  - Low leakage current
- Kelvin emitter for easy drive
- Very low stray inductance
- Lead frames for power connections
- High level of integration
- Internal thermistor for temperature monitoring

#### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

### All ratings @ T<sub>j</sub> = 25°C unless otherwise specified

#### Absolute maximum ratings (Per IGBT)

Symbol	Parameter		Max ratings	Unit
V <sub>CES</sub>	Collector - Emitter Voltage		650	V
т	Continuous Collector Current	$T_C = 25^{\circ}C$	150	
I <sub>C</sub>	Continuous Conector Current	$T_C = 80^{\circ}C$	90	А
I <sub>CM</sub>	Pulsed Collector Current	$T_C = 25^{\circ}C$	300	
$V_{GE}$	Gate – Emitter Voltage		±20	V
PD	Power Dissipation		365	W

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handing Procedures Should Be Followed.

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APTGTQ150TA65TPG - Rev 0



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### Electrical Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I <sub>CES</sub>	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 650V$				150	μΑ
V	Collector Emitter Saturation Voltage	$V_{GE} = 15V$ $I_C = 150A$	$T_j = 25^{\circ}C$		1.65	2.2	V
V <sub>CE(sat)</sub>			$T_{j} = 150^{\circ}C$		1.9		v
V <sub>GE(th)</sub>	Gate Threshold Voltage	$V_{GE} = V_{CE}$ , $I_C = 1.5 \text{mA}$		3.3	4.0	4.7	V
I <sub>GES</sub>	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				360	nA

### Dynamic Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$			9000		
C <sub>oes</sub>	Output Capacitance				150		pF
Cres	Reverse Transfer Capacitance	f = 1 MHz			33		
Q <sub>G</sub>	Gate charge	$V_{GE} = 15V, I_C = 150A$ $V_{CE} = 520V$			360		nC
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switching (25°C)			21		
Tr	Rise Time	$V_{GE} = 15V$			15		
T <sub>d(off)</sub>	Turn-off Delay Time	$V_{Bus} = 400V$ $I_C = 75A$ $R_G = 1\Omega$			180		ns
$T_{\rm f}$	Fall Time				18		
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = 15V$ $V_{Bus} = 400V$ $I_C = 75A$ $R_G = 1\Omega$			20		ns
Tr	Rise Time				15		
T <sub>d(off)</sub>	Turn-off Delay Time				205		
$T_{\rm f}$	Fall Time				26		
Eon	Turn on Energy	$V_{GE} = 15V$ $V_{Bus} = 400V$ $I_C = 75A$ $R_G = 1\Omega$	$T_j = 150^{\circ}C$		2.25		mJ
E <sub>off</sub>	Turn off Energy		$T_j = 150^{\circ}C$		0.9		1113
R <sub>Gint</sub>	Integrated gate resistor				1.7		Ω
R <sub>thJC</sub>	Junction to Case Thermal Resistance					0.41	°C/W

#### Diode ratings and characteristics (per diode)

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit	
V <sub>RRM</sub>	Peak Repetitive Reverse Voltage					650	V	
I <sub>RM</sub>	Reverse Leakage Current	$V_R = 650V$				150	μA	
I <sub>F</sub>	DC Forward Current		$Tc = 25^{\circ}C$		150		А	
V	Diode Forward Voltage	$I_{\rm F} = 150 {\rm A}$	$T_i = 25^{\circ}C$		1.6	2.2	V	
$V_{\rm F}$		$V_{GE} = 0V$	$T_i = 150^{\circ}C$		1.65		v	
t <sub>rr</sub>	Reverse Recovery Time	$I_{\rm T} = 75 \Delta$	$T_j = 25^{\circ}C$		46		ns	
۲r	Reverse Recovery Time		$T_{j} = 150^{\circ}C$		62		115	
0	D	$\frac{v_{\rm R} - 400 v}{di/dt} = 4500 \text{A}/\mu \text{s}$		$T_j = 25^{\circ}C$		1.5		C
Q <sub>rr</sub>	Reverse Recovery Charge		$T_{j} = 150^{\circ}C$		3		μC	
R <sub>thJC</sub>	Junction to Case Thermal Resistance					0.47	°C/W	

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#### Temperature sensor NTC (see application note APT0406 on www.microsemi.com).

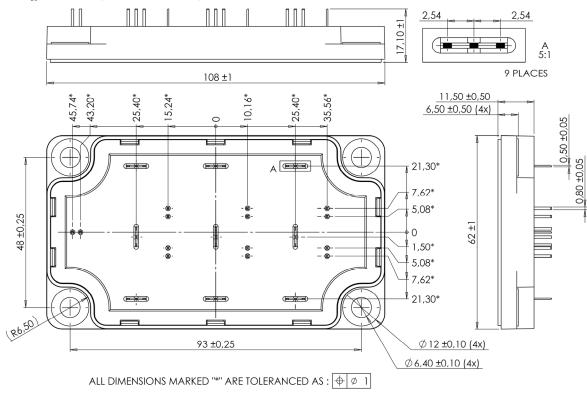
Symbol	Characteristic		Min	Тур	Max	Unit
R <sub>25</sub>	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
B <sub>25/85</sub>	$T_{25} = 298.15 \text{ K}$			3952		Κ
$\Delta B/B$		$T_C=100^{\circ}C$		4		%
	R					

 $R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$  T: Thermistor temperature R<sub>T</sub>: Thermistor value at T

#### Thermal and package characteristics

Symbol	Characteristic			Min	Max	Unit
VISOL	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000		V
T <sub>J</sub>	Operating junction temperature range			-40	175	
T <sub>JOP</sub>	Recommended junction temperature under switching conditions			-40	T <sub>J</sub> max -25	°C
T <sub>STG</sub>	Storage Temperature Range			-40	125	C
T <sub>C</sub>	Operating Case Temperature				125	
Torque	Mounting torque	To heatsink	M6	3	5	N.m
Wt	Package Weight				250	g

#### Package outline (dimensions in mm)



See application note 1902 - Mounting Instructions for SP6-P (12mm) Power Modules on www.microsemi.com

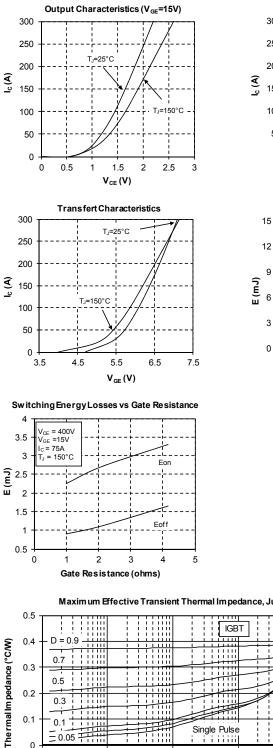
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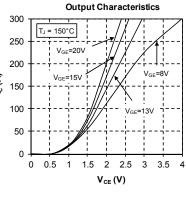
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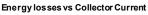


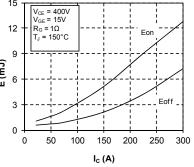
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#### **Typical Performance Curve**

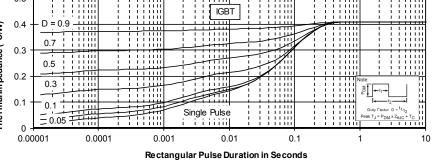








Maxim um Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration

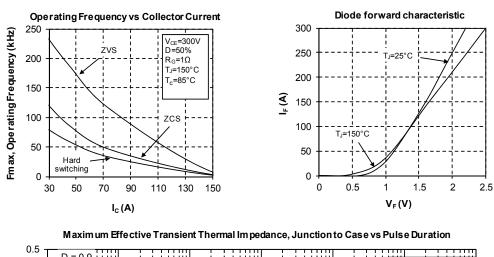


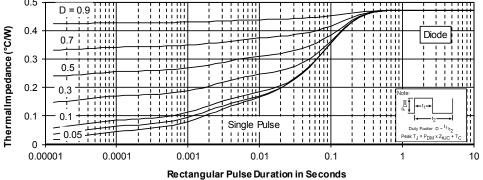
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May, 2016 APTGTQ150TA65TPG - Rev 0

4 - 6







APTGTQ150TA65TPG-Rev 0 May, 2016

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